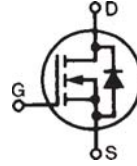


# HiPerFET™ Power MOSFET Q2-Class

## IXFB38N100Q2

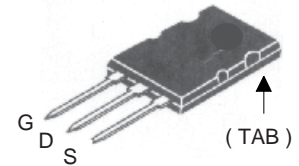
N-Channel Enhancement Mode  
Avalanche Rated, Low  $Q_g$ , Low Intrinsic  $R_G$   
High  $dV/dt$ , Low  $t_{rr}$



$$\begin{aligned} V_{DSS} &= 1000V \\ I_{D25} &= 38A \\ R_{DS(on)} &\leq 250m\Omega \\ t_{rr} &\leq 300ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	1000	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	38	A
$I_{DM}$	$T_C = 25^\circ C$ , pulse width limited by $T_{JM}$	152	A
$I_A$	$T_C = 25^\circ C$	38	A
$E_{AS}$	$T_C = 25^\circ C$	5	J
$dV/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	20	V/ns
$P_D$	$T_C = 25^\circ C$	890	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6 mm (0.063 in.) from case for 10s	300	$^\circ C$
$T_{sOLD}$	Plastic body for 10s	260	$^\circ C$
$F_C$	Mounting force	30..120/6.7..27	N / lbs
<b>Weight</b>		10	g

### PLUS264™( IXFB)



G = Gate                      D = Drain  
S = Source                    TAB = Drain

### Features

- Double metal process for low gate resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance  
- easy to drive and to protect
- Fast intrinsic rectifier

### Applications

- DC-DC converters
- Switched-mode and resonant-mode power supplies, >500kHz switching
- DC choppers
- Pulse generation
- Laser drivers

### Advantages

- PLUS 264™ package for clip or spring mounting
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ C$ , unless otherwise specified)		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8mA$	3.0		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 3 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			250 m $\Omega$

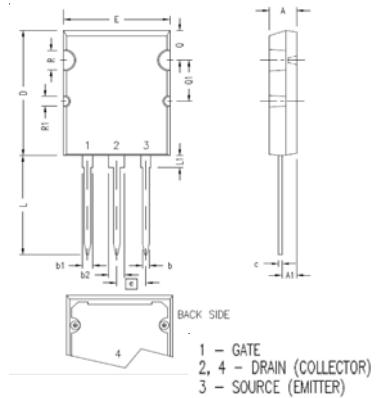
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}, I_D = 0.5 \cdot I_{D25}$ , Note 1	24	40	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		13.5	nF
$C_{oss}$			1035	pF
$C_{rss}$			180	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		25	ns
$t_r$			28	ns
$t_{d(off)}$			57	ns
$t_f$			15	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		250	nC
$Q_{gs}$			60	nC
$Q_{gd}$			105	nC
$R_{thJC}$			0.14	$^\circ\text{C/W}$
$R_{thCS}$		0.13		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			38 A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			152 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$			300 ns
$Q_{RM}$			1.4	$\mu\text{C}$
$I_{RM}$			9	A

Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

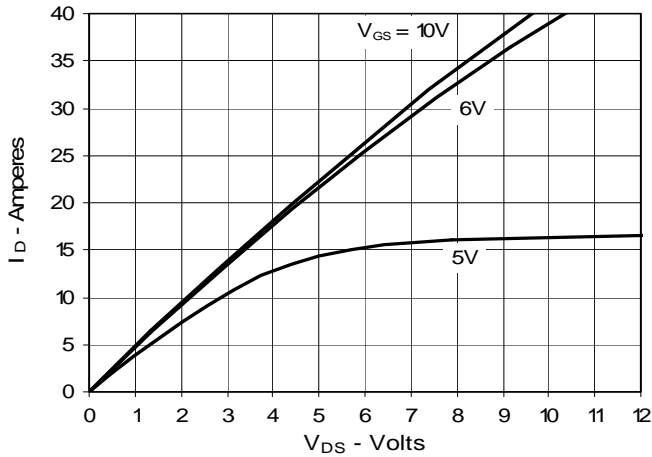
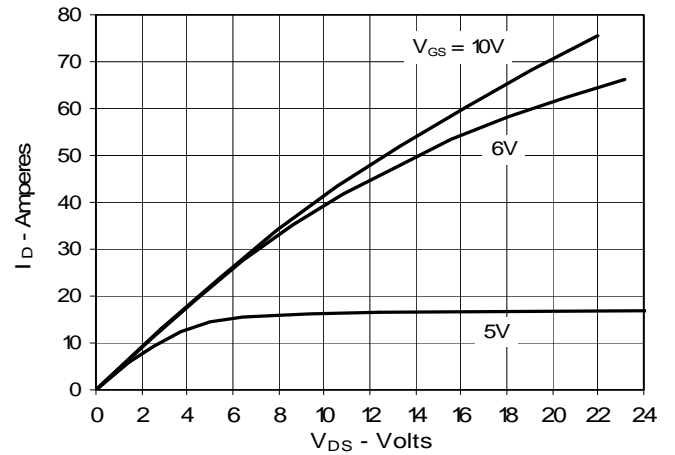
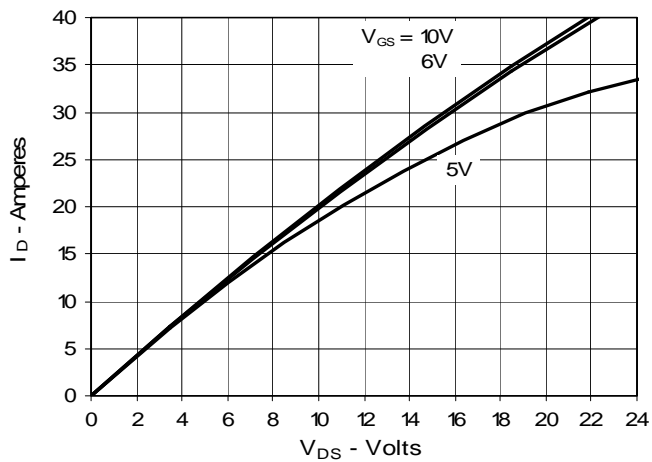
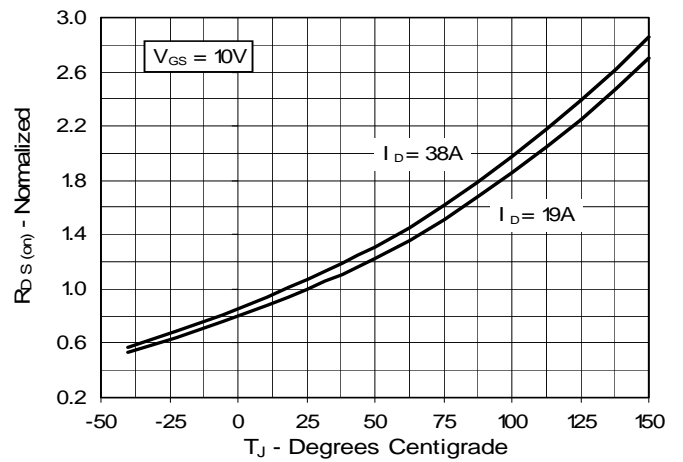
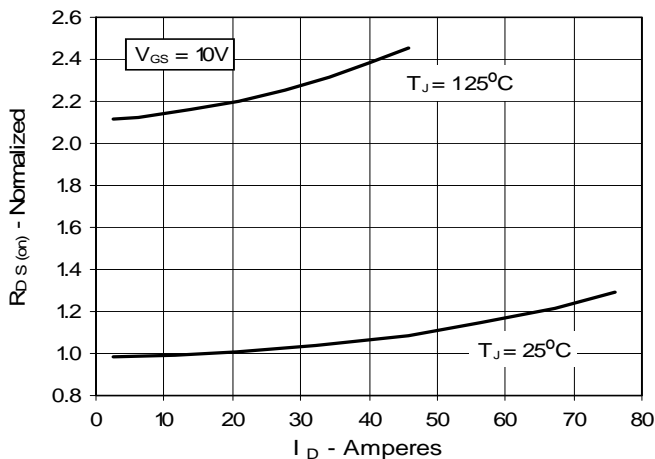
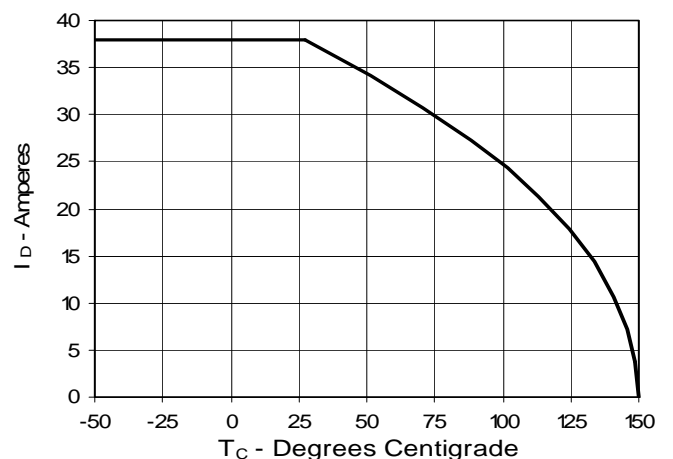
### PLUS264™ (IXFB) Outline

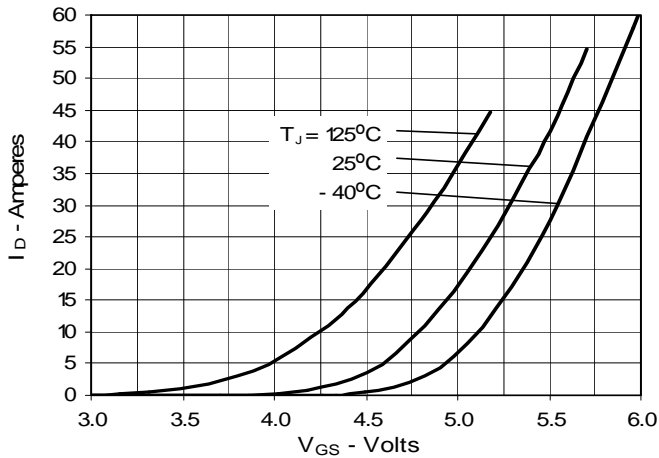
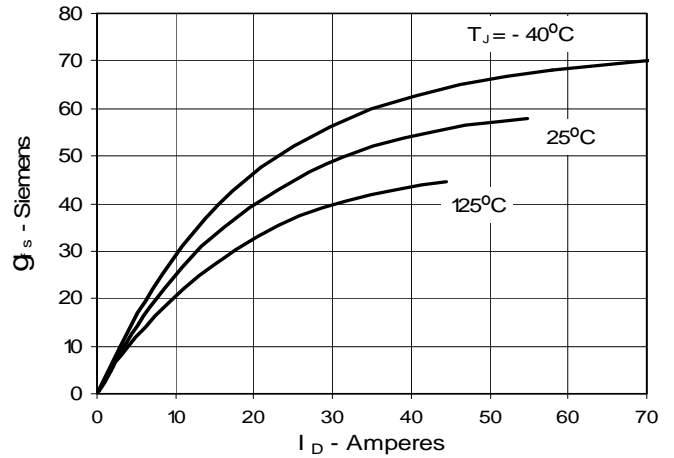
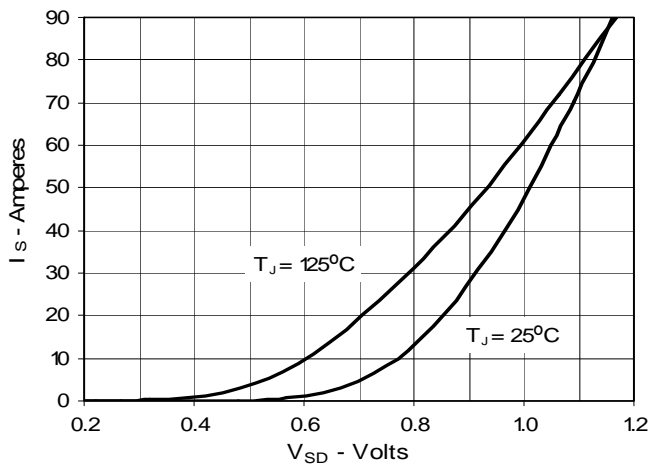
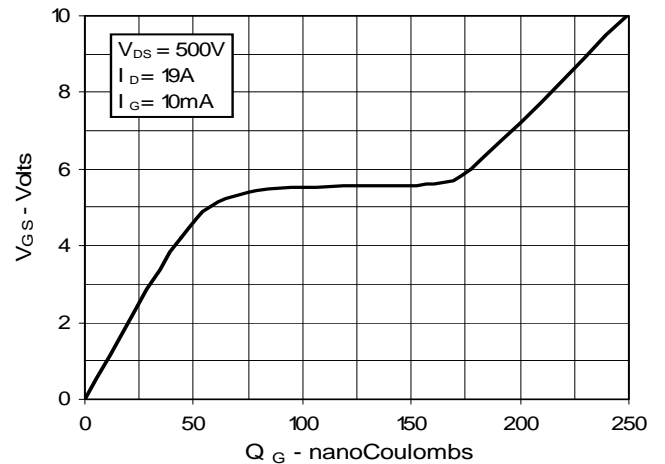
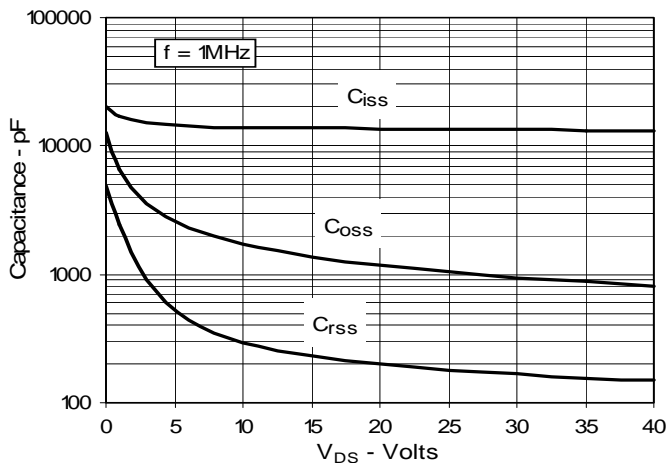


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics  
@ 25°C**

**Fig. 2. Extended Output Characteristics  
@ 25°C**

**Fig. 3. Output Characteristics  
@ 125°C**

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 19A$   
Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 19A$   
Value vs. Drain Current**

**Fig. 6. Drain Current vs.  
Case Temperature**


**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Source Current vs. Source-To-Drain Voltage**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Maximum Transient Thermal Impedance**
